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**HIRAI HIROYUKI
FUKUOKA YOSHITAKA****(54) SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME**

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(57) Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor device which assures higher reliability in the mechanical strength and moisture resistance as the semiconductor device and moreover, can improve integration degree by forming a wiring pattern to the entire part of a multi-layer plate, and also to provide a method of manufacturing the same semiconductor device.

SOLUTION: Conductor bumps 60, 60,... and so on are formed on the wiring pads 41b, 41b of a double-layer plate 52, barrier metal layer 61 and an Au layer 62 are also formed, and a semiconductor element 70 is also formed thereon. Moreover, a prepreg 31 providing an aperture 31a and another double-layer plate 54 are aligned thereon, and these are pressed under the heated condition. At the surface of the semiconductor device 1 obtained, the boundary surface of the insulation resin filling the circumference of the semiconductor element 70 and the double-layer plate 54 does not appear.

